

Technical Data Datasheet 4338, Rev B

HIGH VOLTAGE SILICON CARBIDE SINGLE PHASE FULL WAVE BRIDGE

DESCRIPTION: 2500-VOLT, 5 AMP POWER SILICON CARBIDE SINGLE PHASE FULL WAVE BRIDGE

FEATURES:

- NO RECOVERY TIME OR REVERSE RECOVERY LOSSES
- NO TEMPERATURE INFLUENCE ON SWITCHING BEHAVIOR
- 15000-VOLT HI-POT CAPABILITY

MAXIMUM RATINGS

ALL RATINGS ARE @ T_C = 25 °C UNLESS OTHERWISE SPECIFIED.

SYMBOL	MAX.	UNITS
PIV	2500	Volts
Io	5	Amps
I _{FRM}	30	Amps
I _{FSM}	100	Amps
P _d	100	W
$R_{\theta JC}$	0.5	°C/W
Top, Tstg	-55 to +200	°C
	$\begin{array}{c c} PIV & & & \\ & I_O & & \\ & I_{FRM} & & \\ & I_{FSM} & & \\ & P_d & & \\ & R_{\theta JC} & & \end{array}$	$\begin{array}{c cccc} PIV & 2500 \\ & I_O & 5 \\ & & & & & & \\ & I_{FRM} & 30 \\ & & & & & & \\ & I_{FSM} & 100 \\ & & P_d & 100 \\ & & & & & \\ & P_{d} & 0.5 \\ & & & & \\ & Top, Tstg & -55 to \\ \end{array}$

* Note: SiC semiconductors will handle at or above this operating and storage temperature. However, extended operational use of the packaged device above 175C may reduce its future performance. All qualification testing and screening per MIL-PRF-19500 will only be performed to 175C.

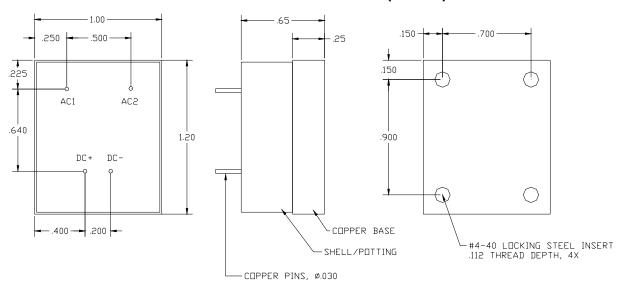
ELECTRICAL CHARACTERISTICS

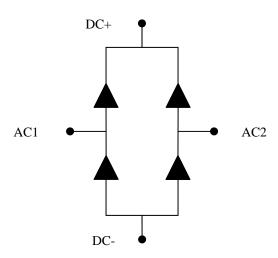
CHARACTERISTIC	TYP	MAX.	UNITS
MAXIMUM FORWARD VOLTAGE DROP ($I_f = 5$ A PER LEG) V_f $T_J = 25$ °C	5	5.50	
T _J =150 °C	7.5	9.00	Volts
MAXIMUM REVERSE CURRENT (2500V PIV PER LEG) I_r $T_J = 25$ °C	0.05	0.40	
T _J = 150 °C	0.10	2.00	mA
JUNCTION CAPACITANCE (V _r =5V) per leg C _T	240		pF
TOTAL CAPACITANCE CHARGE (V _R =2500V, I _F =5A, di/dt=500A/ μ s and T _J =25°C) Q _C per leg	28	N/A	nC

SENSITRON SHB636053E

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MECHANICAL DIMENSIONS (inches)





Application Note: Customers should be aware that at the current stage of technical development of SiC, the reverse avalanche capabilities of the device are limited. Customer designs will need to accommodate these limitations and avoid exposure of the device to this and other potentially damaging conditions in their applications.

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